

**V1.0 Datasheet** 

#### **P-Channel 30V MOSFET**

#### **FEATURES**

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

# **Application**

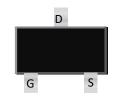
- Portable Devices
- ■Consumer Electronics

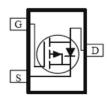
# Mechanical

●Case: SOT-23 Package

# PRODUCTY SUMMARY $V_{DS}$ $R_{DS(on)} m(Ω)$ $I_{D}(A)$ -30 63 $@V_{GS}$ =-10.0V -2.6 63 $@V_{GS}$ =-2.5V -2.1

**SOT-23** 





## **Packing Information**

| Package | Packing       |  |
|---------|---------------|--|
| SOT-23  | 3Kpcs/7" Reel |  |

| Maximum Ratings (T <sub>A</sub> =25°C unless otherwise specified) |                                   |            |      |  |  |  |
|---|-----------------------------------|------------|------|--|--|--|
| Parameter   | Symbol                            | Limit      | Unit |  |  |  |
| Drain-Source Voltage  | V <sub>DS</sub>                   | -30        | V    |  |  |  |
| Gate-Source Voltage   | V <sub>GS</sub>                   | ±12        | V    |  |  |  |
| Continuous Drain Current 1)                                       | I <sub>D</sub>                    | -2.1       | А    |  |  |  |
| Maximum Power Dissipation   | P <sub>D</sub>                    | 0.35       | W    |  |  |  |
| Pulsed Drain Current 2)   | I <sub>DM</sub>                   | -8.4       | Α    |  |  |  |
| Operating Junction and Storage Temperature Range                  | T <sub>J</sub> , T <sub>STG</sub> | -55 to 150 | °C   |  |  |  |

| Typical Thermal Resistance             |                 |       |      |  |
|--|-----------------|-------|------|--|
| Parameter                              | Symbol          | Limit | Unit |  |
| Junction-to-Ambient Thermal Resistance | $R_{\theta JA}$ | 100   | °C/W |  |

#### Note

R0JA is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper

www.mo-semi.com Revision: V1.0



| Characteristics                  | Symbol              | Test Condition   | Limits |     |      |      |
|----------------------------------|---------------------|--|--------|-----|------|------|
|                                  |                     |  | Min    | Тур | Max  | Unit |
|                                  |                     | Static   |        |     |      |      |
| Drain-Source Breakdown Voltage   | B <sub>VDSS</sub>   | $V_{GS} = 0V, I_{D} = -250uA$                                | -30    | -   | -    | V    |
| Gate Threshold Voltage           | V <sub>GS(th)</sub> | $V_{DS}=V_{GS}$ , $I_{D}=-250uA$                             | -0.5   | -1  | -1.3 | V    |
|                                  |                     | V <sub>GS</sub> =-10.0V, I <sub>D</sub> =-2.6A               | -      | 45  | 55   | mΩ   |
| Drain-Source On-State Resistance | R <sub>DS(on)</sub> | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.5A                | -      | 52  | 63   | mΩ   |
|                                  |                     | V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-2.1A                | -      | 71  | 86   | mΩ   |
| Zero Gate Voltage Drain Current  | I <sub>DSS</sub>    | V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V                   | -      | -   | -1   | uA   |
| Gate-Source Leakage Current      | I <sub>GSS</sub>    | V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V                   |        |     | ±100 | nA   |
|                                  |                     |  |        |     |      |      |
|                                  |                     | Dynamic <sup>3)</sup>  |        |     |      |      |
| Total Gate Charge                | $Q_g$               | 4514   | ı      | 19  | -    | nC   |
| Gate-Source Charge               | $Q_{gs}$            | $V_{DS}$ =-15V, $I_{D}$ =-3.6A, $V_{GS}$ =-10V               | -      | 2   | -    | nC   |
| Gate-Drain Charge                | $Q_{gd}$            | 36   | ı      | 2.2 | -    | nC   |
| Input Capacitance                | C <sub>iss</sub>    | V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V,<br>f=1.0MHZ      | -      | 994 | -    | pF   |
| Output Capacitance               | C <sub>oss</sub>    |  | -      | 78  | -    | pF   |
| Reverse Transfer Capacitance     | C <sub>rss</sub>    |  | -      | 58  | -    | pF   |
|                                  |                     |  |        |     |      |      |
|                                  |                     | Switching  |        |     |      |      |
| Turn-On Delay Time               | t <sub>d(on)</sub>  |  | -      | 4.6 | -    | ns   |
| Turn-On Rise Time                | t <sub>r</sub>      | $V_{DD}$ =-15V, $I_{D}$ =-3.6A, $V_{GS}$ =-10V,RG=6 $\Omega$ | ı      | 22  | -    | ns   |
| Turn-Off Delay Time              | t <sub>d(off)</sub> |  | -      | 41  | -    | ns   |
| Turn-Off Fall Time               | t <sub>f</sub>      |  | -      | 25  | -    | ns   |
|                                  |                     |  |        |     |      |      |
|                                  | Dra                 | ain-Source Diode   |        | I   |      |      |
| Maximum Continuous Drain-Source  | I <sub>S</sub>      | -  | -      | -   | -1.5 | Α    |
| Diode Forward Voltage            | V <sub>SD</sub>     | I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V                   | -      | -   | -1.2 | V    |

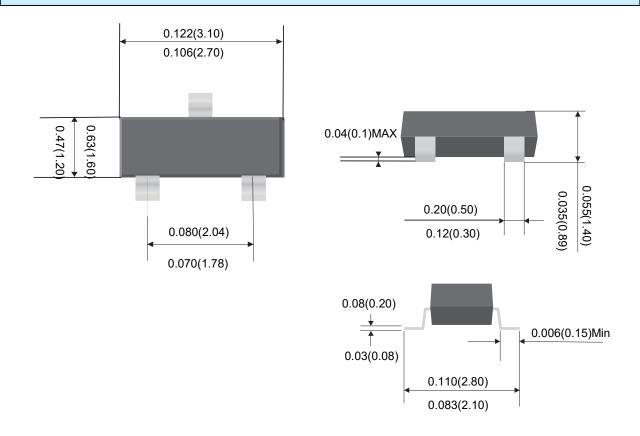
## Note:

- Pulse width<300us, Duty cycle<2%</li>
  Fused current that based on wire numbers and diameter
  Guaranteed by design, not subject to production testing.

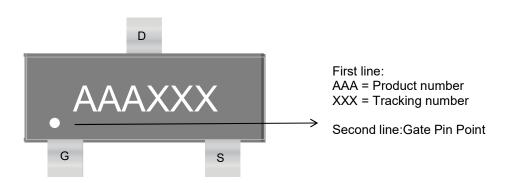
Revision: V1.0 www.mo-semi.com



## Package Outline Dimensions (inches and millimeters)



#### **Marking Information**



Motive reserves the right to make changes without further notice to any products herein. Motive makes no warranty `representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motive assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in Motive data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motive does not convey any license under its patent rights or the rights of others. Motive products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motive product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motive products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motive and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims 'costs' damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motive was negligent regarding the design or manufacture of the part.

www.mo-semi.com Revision: V1.0